

Features

- Low operating voltage: 5V
- Ultra low capacitance: 0.4pF
- Ultra low leakage: nA level
- Low clamping voltage
- -IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
- -IEC61000-4-4 (EFT) 40A (5/50ns)
- -IEC61000-4-5 (Lightning) 8A (8/20 μs)
- 2-pin leadless package
- These are Pb-Free Devices
- Response Time is Typically < 1 ns

pin to pin AQ4337-01ETG

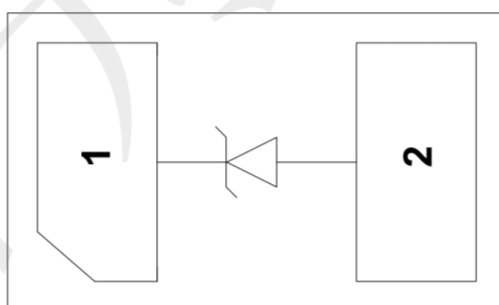
Mechanical Characteristics

- Package: DFN1006-2(0402)
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound
- Terminal Connections: See Diagram Below
- -IEC 61000-4-2 (ESD) immunity test

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- USB 2.0 power and data line

Dimensions and Pin Configuration



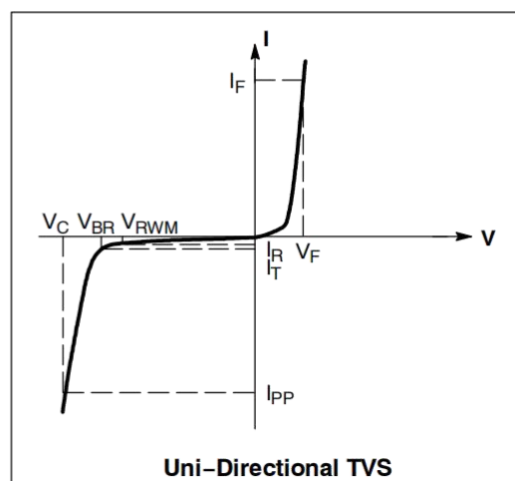
Absolute Maximum Ratings (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	P _{pk}	84	W
Peak Pulse Current (8/20μs)	I _{pp}	8	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	±30 ±30	KV
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}	--	--	5	V	
Breakdown Voltage	V _{BR}	6	--	9.5	V	I _T = 1mA
Reverse Leakage Current	I _R	--	--	100	nA	V _{RWM} = 5V
Clamping Voltage	V _C	--	5.5	7	V	I _{pp} = 1A (8x 20us pulse)
Clamping Voltage	V _C	--	7.5	9	V	I _{pp} = 6A (8x 20us pulse)
Clamping Voltage	V _C	--	8.5	10.5	V	I _{pp} = 8A (8x 20us pulse)
Junction Capacitance	C _J	--	0.4	0.65	pF	V _R = 0V, f = 1MHz

Symbol	Parameter
I _{pp}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{pp}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
I _F	Forward Current
V _F	Forward Voltage @ I _F
P _{pk}	Peak Power Dissipation
C	Capacitance @ V _R = 0 and f = 1.0 MHz



Characteristic Curves

Fig1. 8/20 μ s Pulse Waveform

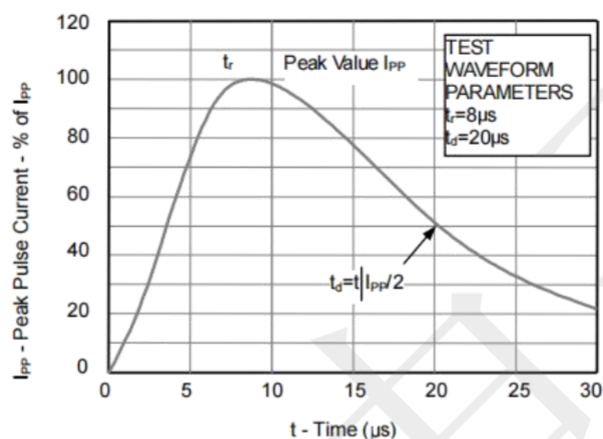


Fig2. ESD Pulse Waveform (according to IEC 61000-4-2)

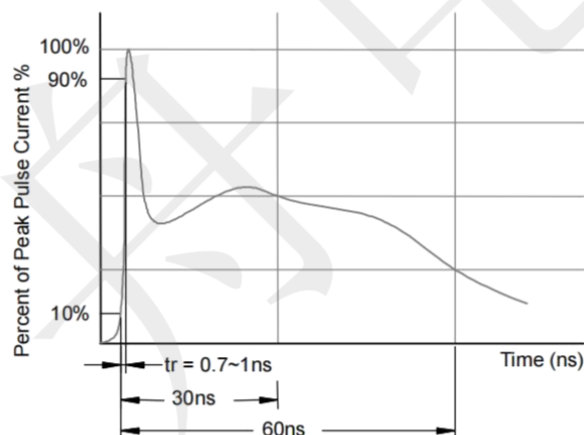
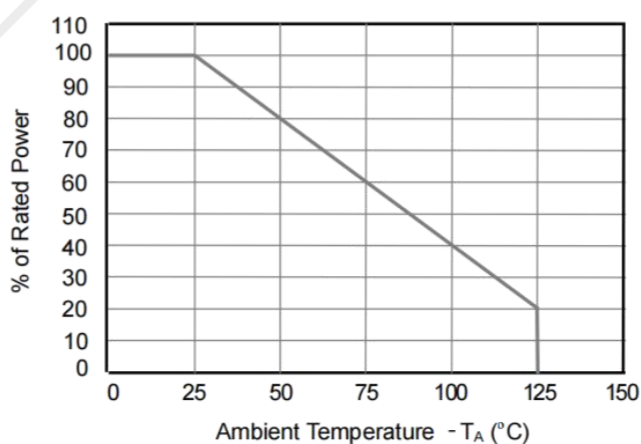
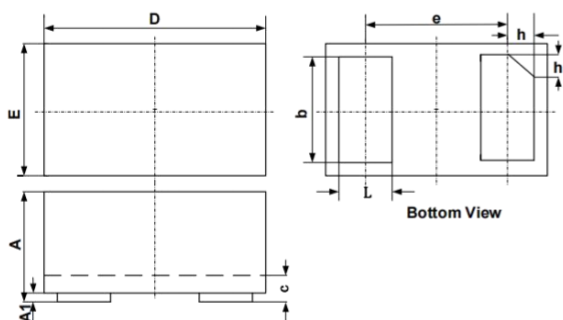


Fig3. Power Derating Curve



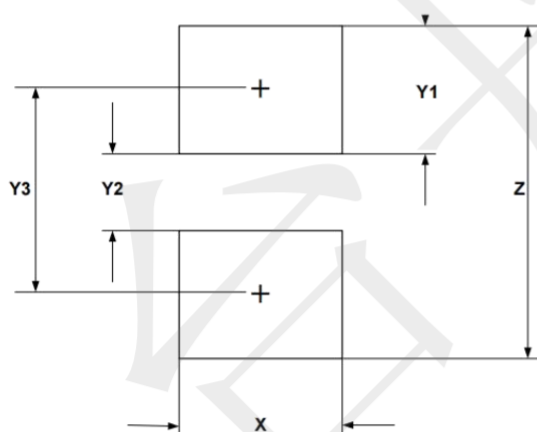
Package Outline & Dimensions

DFN1006-2 (0402)



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.20	0.25	0.30	0.008	0.010	0.012
h	0.07	0.12	0.17	0.003	0.005	0.007

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.60	0.024
Y1	0.50	0.020
Y2	0.30	0.012
Y3	0.80	0.032
Z	1.30	0.052